



reduces the time for which the film 28 for providing a ferroelectric 18 is exposed to a dry-etching plasma atmosphere. Thus, the ferroelectric 18 can be prevented from being deteriorated in characteristics by the effects of a plasma.

At page 10, replace the paragraph beginning at line 6 with the following:

Meanwhile, as shown in Figure 10, a first electrode portion 16a may be formed at a corner of the hollow 14 by a process including spin coating (e.g. sol-gel technique) so that a second electrode portion 16b can be formed to provide a lower electrode 16. In this case, if the second electrode portion 16b is formed by a process including a spin coat technique (e.g. sol-gel technique), it is possible to decrease an amount of depression to be caused in a top surface center thereof upon baking the lower electrode 16. Meanwhile, if the second electrode portion 16b, or first conductive film 26b, is formed by sputtering, the variation in crystalline orientation is reduced in a top surface of the lower electrode 16, as shown in Figure 11. This serves to stabilize a crystalline state of the ferroelectric 18 (Figure 10) to be formed on the lower electrode 16. Furthermore, if the first electrode portion 16a is formed over the entire bottom surface of the hollow 14 as shown in Figure 12, the second electrode portion 16b can be made thin in thickness by a corresponding amount to the film thickness of the first electrode portion 16a. This reduces the amount of etching to be conducted in the etching process.

IN THE CLAIMS:

Please cancel Claims 6-14 without prejudice to incorporating the same in a divisional application to be filed.

Please amend Claim 1 by rewriting the same as follows: